

### ● General Description

The AGM13T15C combines advanced trench MOSFET technology with a low resistance package to provide extremely low  $R_{DS(ON)}$ .

This device is ideal for load switch and battery protection applications.

### ● Features

- Advance high cell density Trench technology
- Low  $R_{DS(ON)}$  to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance
- 100% Avalanche tested
- 100% DVDS tested

### ● Application

- MB/VGA Vcore
- SMPS 2<sup>nd</sup> Synchronous Rectifier
- POL application
- BLDC Motor driver

### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AGM13T15C	AGM13T15C	TO-220	---	---	1000

**Table 1. Absolute Maximum Ratings (TA=25°C)**

Symbol	Parameter	Value	Unit
VDS	Drain-Source Voltage (VGS=0V)	135	V
VGS	Gate-Source Voltage (VDS=0V)	±20	V
ID	Drain Current-Continuous(Tc=25°C) <b>(Note 1)</b>	58	A
	Drain Current-Continuous(Tc=100°C)	39	A
IDM (pluse)	Drain Current-Pulsed <b>(Note 2)</b>	232	A
PD	Maximum Power Dissipation(Tc=25°C)	120	w
	Maximum Power Dissipation(Tc=100°C)	60	w
EAS	Avalanche energy <b>(Note 3)</b>	21	mJ
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 175	°C

**Table 2. Thermal Characteristic**

Symbol	Parameter	Typ	Max	Unit
RθJA	Thermal Resistance Junction-ambient (Steady State) <sup>1</sup>	---	62.5	°C/W
RθJC	Thermal Resistance Junction-Case <sup>1</sup>	---	1.25	°C/W

### Product Summary

BVDSS	RDSON	ID
135V	15.5mΩ	58A

### TO-220 Pin Configuration

**Table 3. Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>On/Off States</b>						
BVDSS	Drain-Source Breakdown Voltage	VGS=0V ID=250μA	135	147	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=135V,VGS=0V	--	--	1	μA
IGSS	Gate-Body Leakage Current	VGS=±20V,VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS,ID=250μA	2	2.8	4	V
gFS	Forward Transconductance	VDS=5V,ID=5A	--	17	--	S
RDS(on)	Drain-Source On-State Resistance	VGS=10V, ID=10A	--	15.5	21	mΩ
<b>Dynamic Characteristics</b>						
Ciss	Input Capacitance	VDS=40V,VGS=0V, F=1MHZ	--	1935	--	pF
Coss	Output Capacitance		--	145	--	pF
Crss	Reverse Transfer Capacitance		--	11	--	pF
Rg	Gate resistance	VGS=0V, VDS=0V,f=1.0MHz	--	2.8	--	Ω
<b>Switching Times</b>						
td(on)	Turn-on Delay Time	VGS=10V,VDS=75V, RGEN=3Ω, RL=7.5Ω	--	10	--	nS
tr	Turn-on Rise Time		--	6.5	--	nS
td(off)	Turn-Off Delay Time		--	16	--	nS
tf	Turn-Off Fall Time		--	7.0	--	nS
Qg	Total Gate Charge	VGS=10V, VDS=75V, ID=20A	--	33	--	nC
Qgs	Gate-Source Charge		--	7.2	--	nC
Qgd	Gate-Drain Charge		--	7.2	--	nC
<b>Source-Drain Diode Characteristics</b>						
ISD	Source-Drain Current(Body Diode)		--	--	58	A
VSD	Forward on Voltage	VGS=0V,IS=20A	--	--	1.2	V
trr	Reverse Recovery Time	IF=20A , dI/dt=100A/μs , TJ=25°C	--	30	--	ns
Qrr	Reverse Recovery Charge		--	135	--	nc

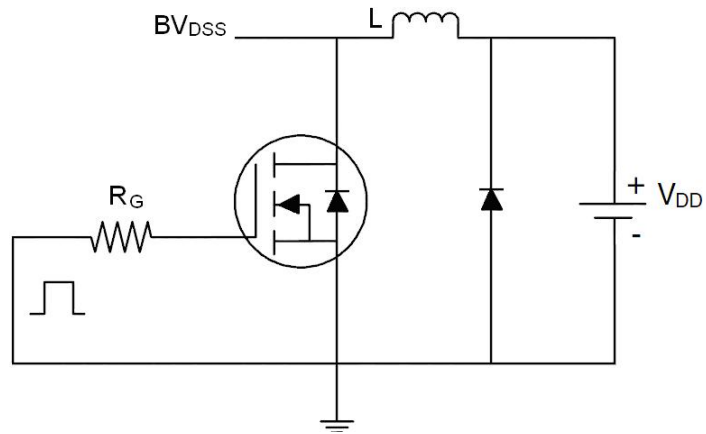
Notes 1.The maximum current rating is package limited.

Notes 2.Repetitive Rating: Pulse width limited by maximum junction temperature

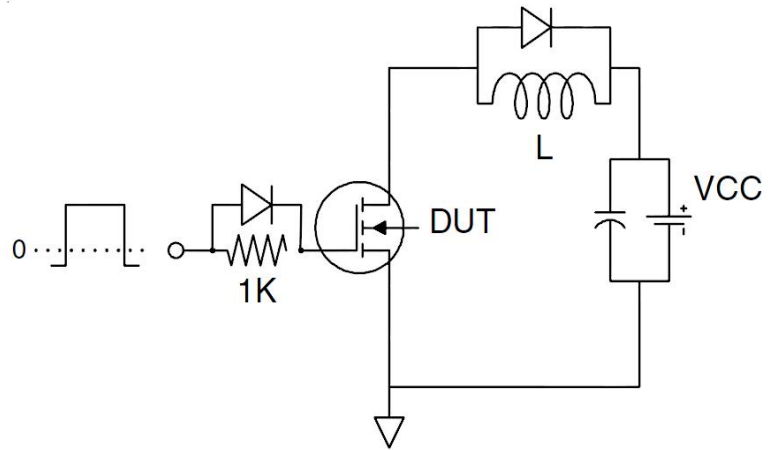
Notes 3.EAS condition: T<sub>J</sub>=25°C,VDD=50V,Vgs=10V,ID=20.5A, L=0.1mH,RG=25ohm

**Test Circuit**

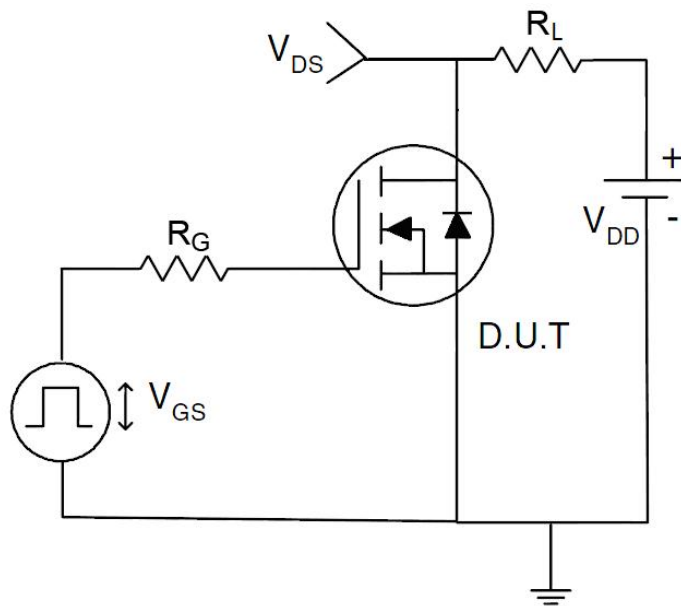
**1) E<sub>AS</sub> test Circuit**



**2) Gate charge test Circuit**



**3) Switch Time Test Circuit**



Typical Electrical and Thermal Characteristics

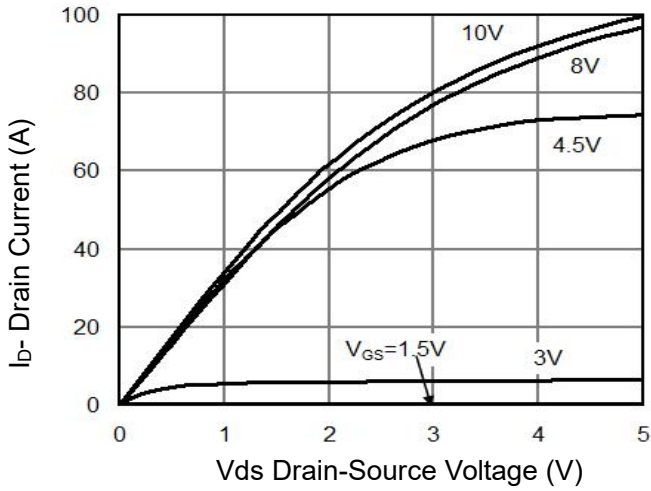


Figure 1 Output Characteristics

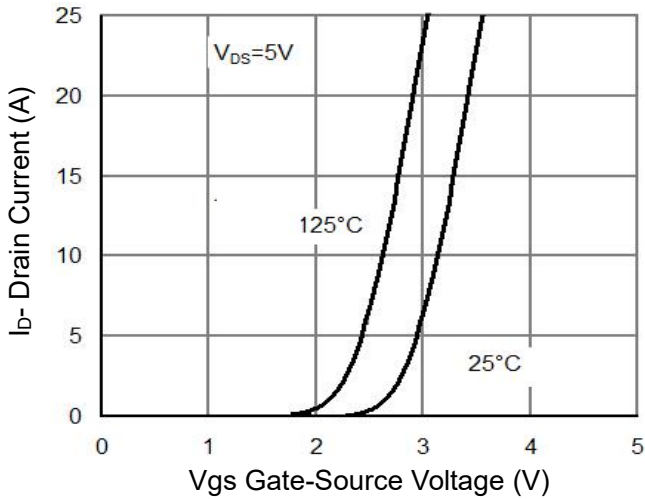


Figure 2 Transfer Characteristics

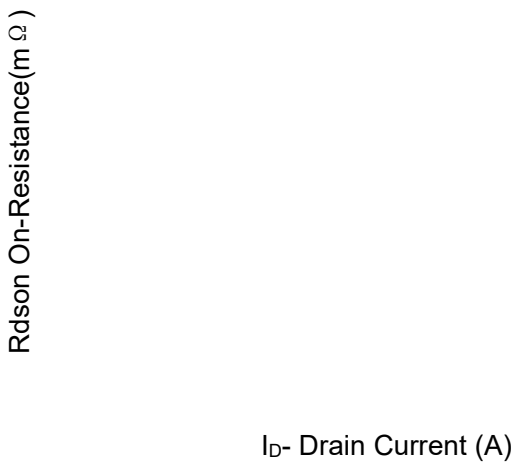


Figure 3 Rdson- Drain Current

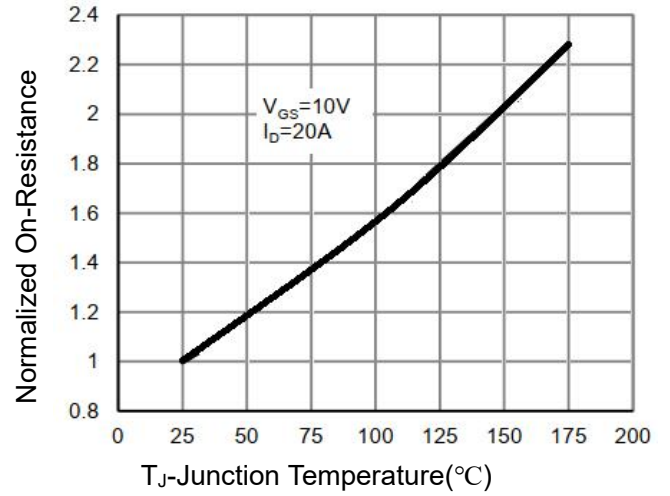


Figure 4 Rdson-Junction Temperature

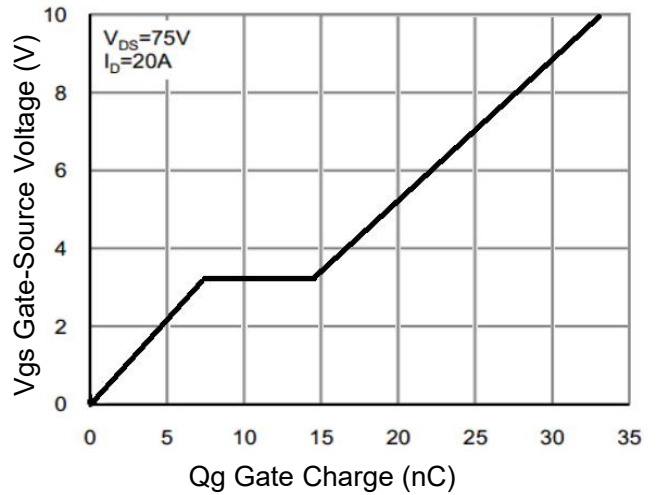


Figure 5 Gate Charge

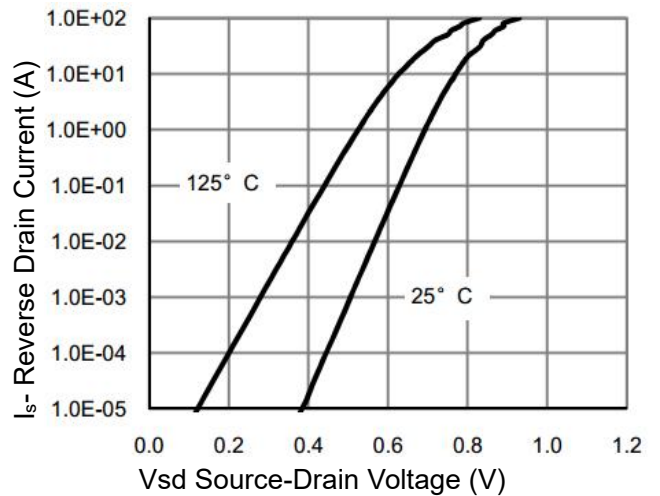


Figure 6 Source- Drain Diode Forward

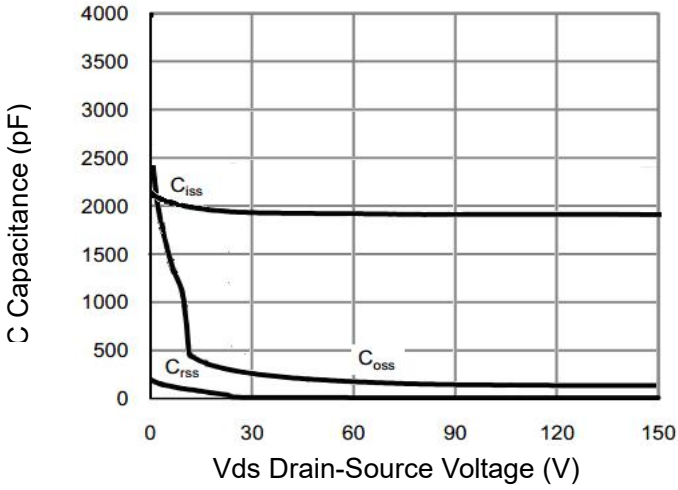


Figure 7 Capacitance vs Vds

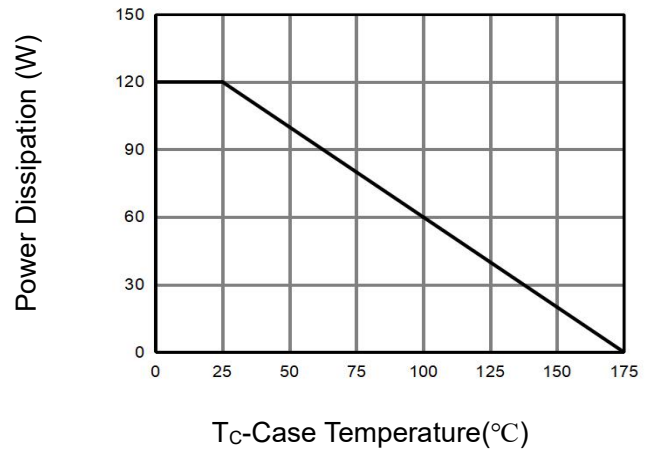


Figure 9 Power De-rating

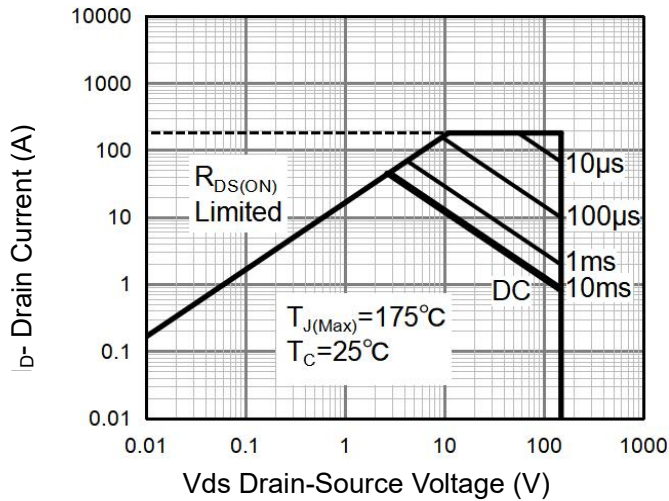


Figure 8 Safe Operation Area (Note3)

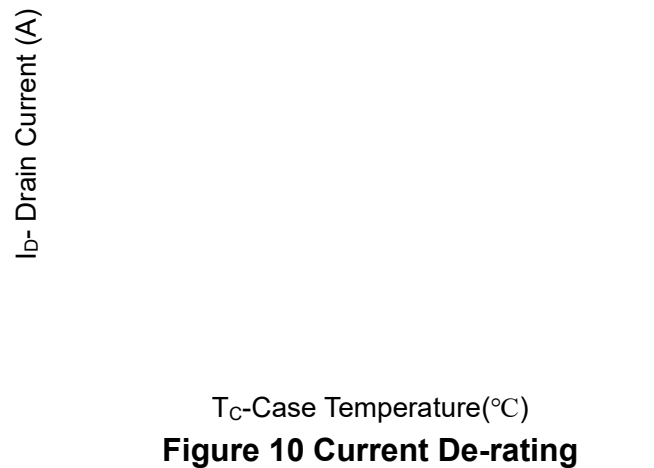


Figure 10 Current De-rating

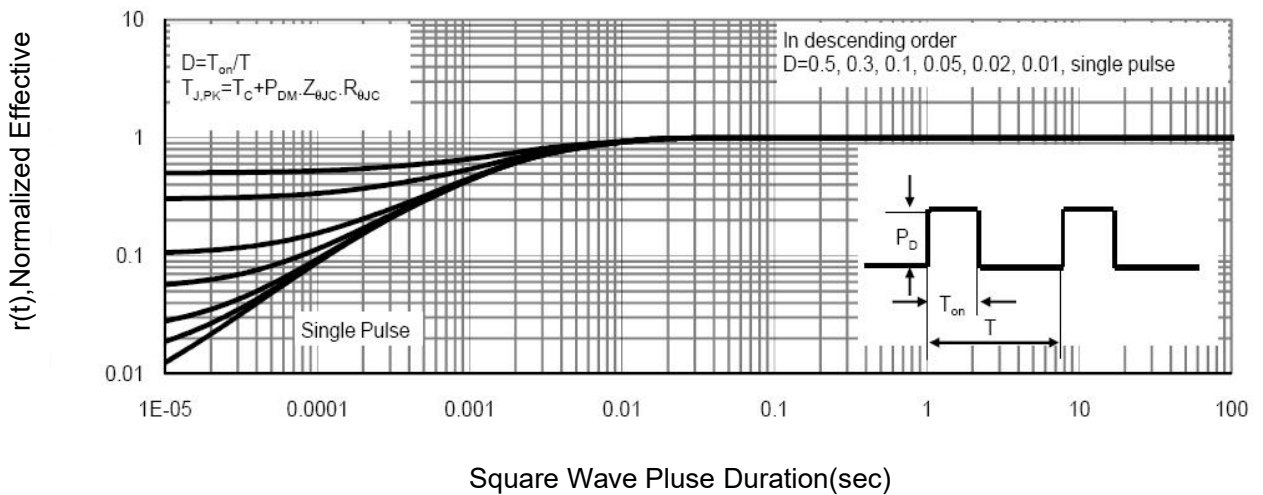


Figure 11 Normalized Maximum Transient Thermal Impedance

# TO-220 PACKAGE INFORMATION


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